

IN THE CLAIMS:

Please amend claims 1-7, 12, 14 and 19 as follows:

1.(Twice Amended) A semiconductor-laser excited solid state laser apparatus
comprising:

51 a semiconductor laser unit including an internal resonator; and

a solid state laser element which emits laser light in response to excitation light
from said semiconductor laser unit;

wherein said internal resonator has a length of at least 0.8 mm, with said internal
resonator length being dependent upon a characteristic of said solid state laser element.

12 2.(Amended) A semiconductor-laser-excited solid state laser apparatus according
to claim 1, wherein said internal resonator has a length of at least 1 mm.

3.(Amended) A semiconductor-laser-excited solid state laser apparatus according
to claim 1, wherein said internal resonator has a length of at least 1.5 mm.

33 112 4.(Twice Amended) A semi conductor-laser excited solid state laser apparatus,
comprising:

a semiconductor laser unit including an internal resonator having a length of at
least 0.8 mm;

a solid state laser element which emits laser light in response to excitation light
from said semiconductor laser unit.

a solid state laser resonator having a solid state laser resonator length, wherein
said solid state laser includes said solid state laser element and a mirror arranged outside of said

13 solid state laser element, with said internal resonator length being independent of said solid state laser resonator length; and

a wavelength conversion element arranged in said solid state laser resonator, which generates a second harmonic wave.

14 5.(Amended) A semiconductor-laser-excited solid state laser apparatus according to claim 4, wherein said internal resonator has a length of at least 1 mm.

6.(Amended) A semiconductor-laser-excited solid state laser apparatus according to claim 4, wherein said internal resonator has a length of at least 1.5 mm.

7.(Amended) A semi conductor-laser excited solid state laser apparatus as claimed in claim 1 wherein said internal resonator length is dependent upon an absorption band of said solid state laser element.

15 12.(Amended) A semi conductor-laser excited solid state laser apparatus as claimed in claim 1 wherein said internal resonator length is selected to cause a wavelength of said excitation light to remain within an absorption band of said solid state laser element.

16 14.(Amended) A semi conductor-laser excited solid state laser apparatus as claimed in claim 4 wherein said internal resonator length is selected based upon an absorption band of said solid state laser element.

17 19.(Amended) A semi conductor-laser excited solid state laser apparatus as claimed in claim 4 wherein said internal resonator length is selected to cause a wavelength of said excitation light to remain within an absorption band of said solid state laser element.
